

Silicon NPN Power Transistors

2SD200

DESCRIPTION

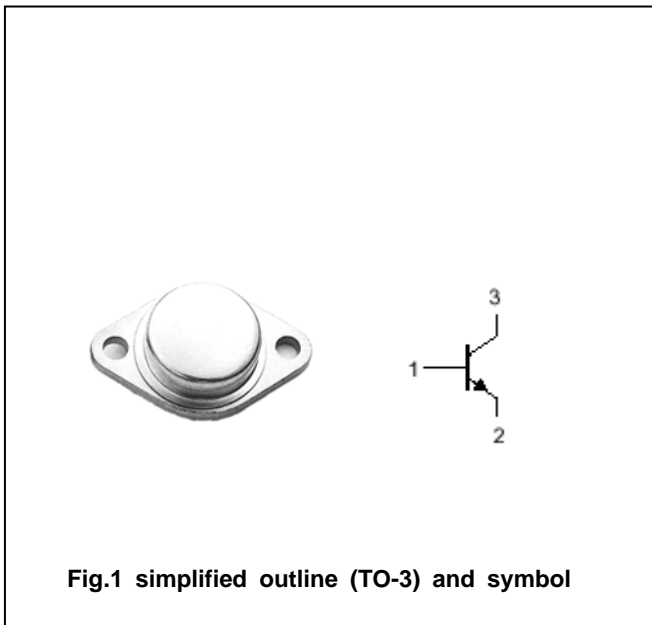
- With TO-3 package
- High voltage ,high reliability
- Wide area of safe operation

APPLICATIONS

- For color TV horizontal output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2.5	A
P_C	Collector power dissipation	$T_C=90^\circ\text{C}$	10	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	600			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.6A			8.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.6A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =500V; I _E =0			10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			100	μ A
h _{FE-1}	DC current gain	I _C =0.5A ; V _{CE} =5V	8			
h _{FE-2}	DC current gain	I _C =2A ; V _{CE} =5V	2.5			

PACKAGE OUTLINE

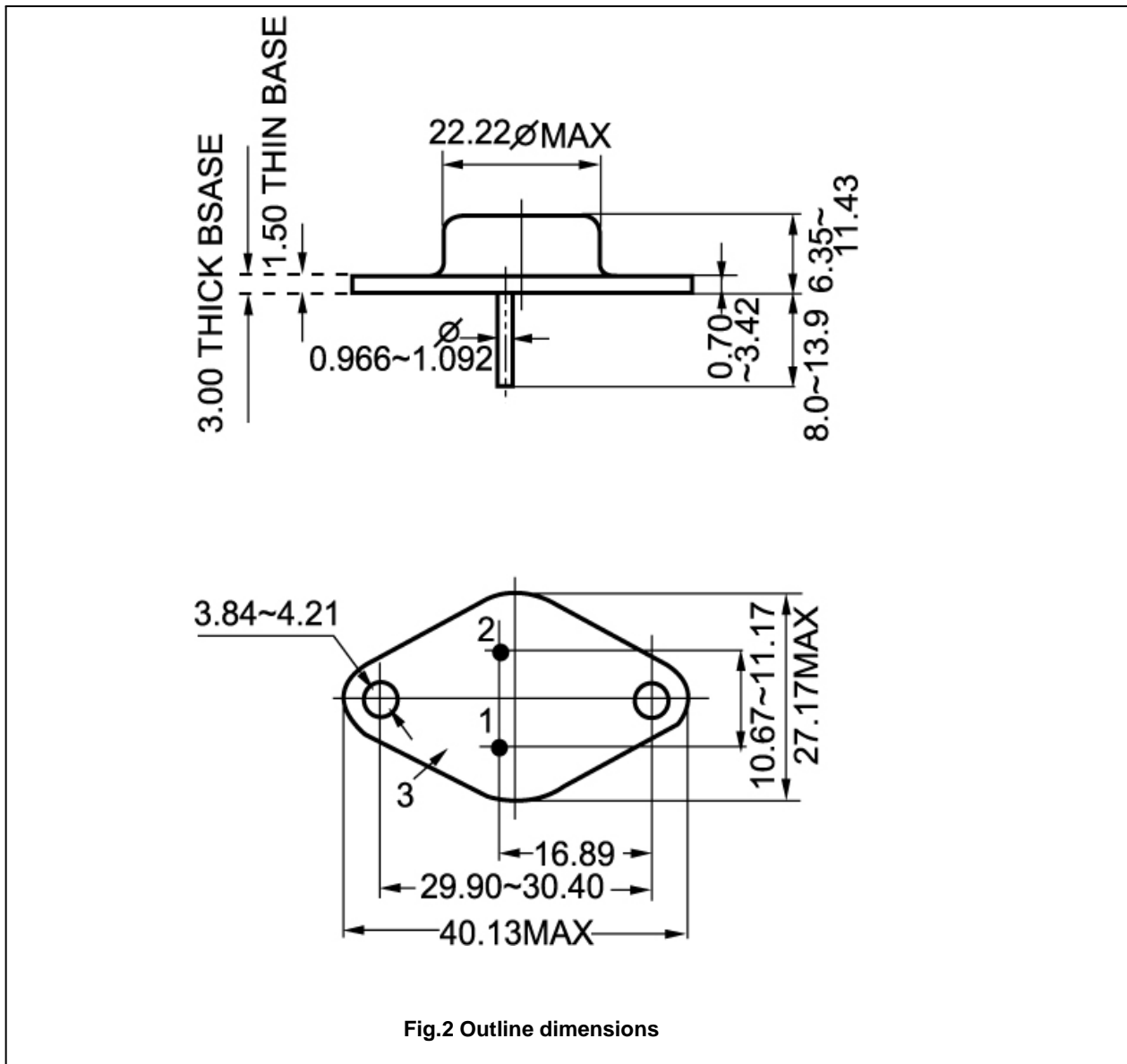


Fig.2 Outline dimensions